

CMXT2907A
SURFACE MOUNT
DUAL PNP
SILICON TRANSISTORS



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT2907A type is a dual PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

MARKING CODE: X2F



MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CB0}	60
V_{CEO}	60
V_{EBO}	5.0
I_C	600
P_D	350
T_J, T_{stg}	-65 to +150
Θ_{JA}	357

UNITS

V
V
V
mA
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=50\text{V}$		10	nA
I_{CBO}	$V_{CB}=50\text{V}, T_A=125^\circ\text{C}$		10	μA
I_{CEV}	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$		50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.6	V
h_{FE}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	75		
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	100		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	100		
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50		
f_T	$V_{CE}=20\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	200		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF
C_{ib}	$V_{BE}=2.0\text{V}, I_C=0, f=1.0\text{MHz}$		30	pF
t_{on}	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	45	ns	
t_d	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	10	ns	
t_r	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	40	ns	
t_{off}	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		100	ns
t_s	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		80	ns
t_f	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$		30	ns

R3 (12-February 2010)

CMXT2907A

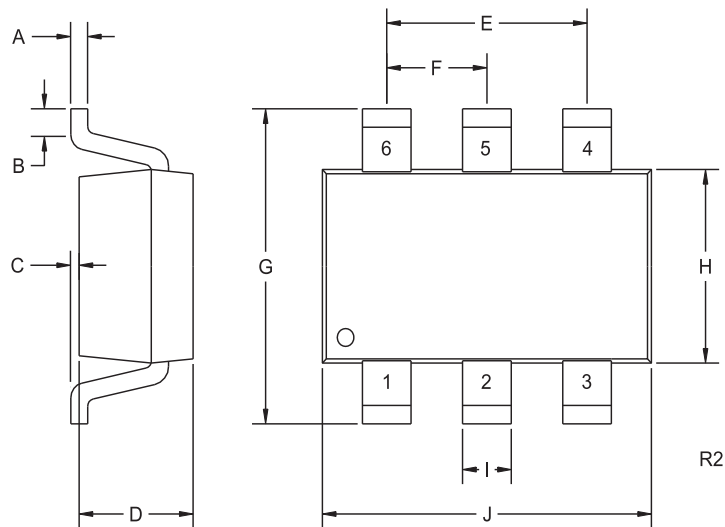
SURFACE MOUNT

DUAL PNP

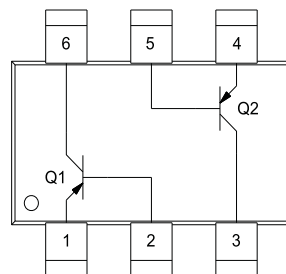
SILICON TRANSISTORS



SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X2F

R3 (12-February 2010)